

D45JCT120V

1200V 45A

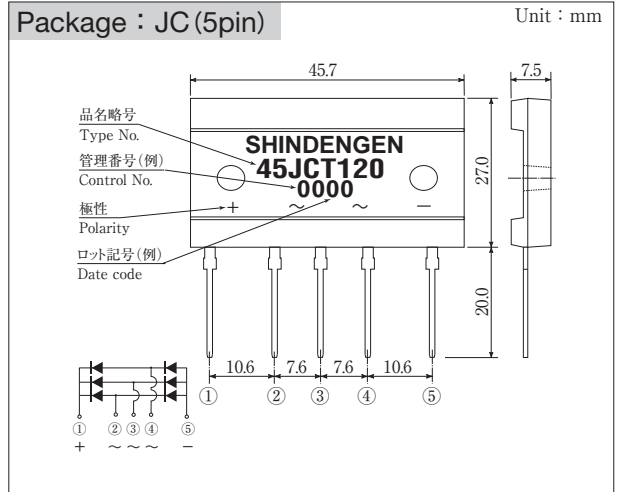
特長

- 薄型 SIP
- UL E142422

Feature

- Compact SIP
- UL E142422

■ 外観図 OUTLINE



外形図については新電元 Web サイトをご参照下さい。捺印表示については捺印仕様をご確認下さい。
 For details of the outline dimensions, refer to our web site. As for the marking, refer to the specification "Marking, Terminal Connection".

■ 定格表 RATINGS

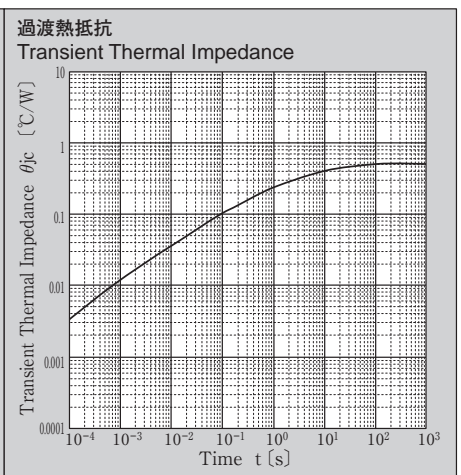
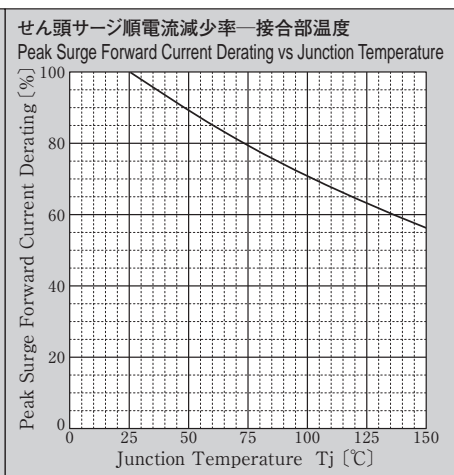
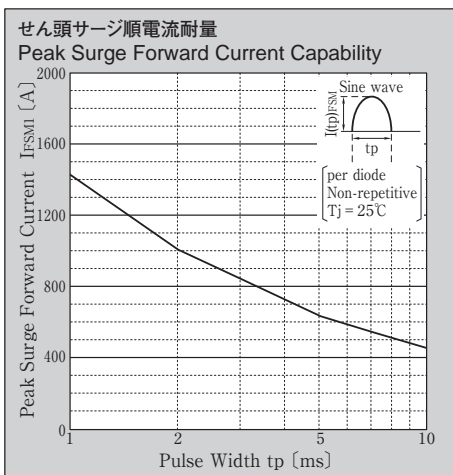
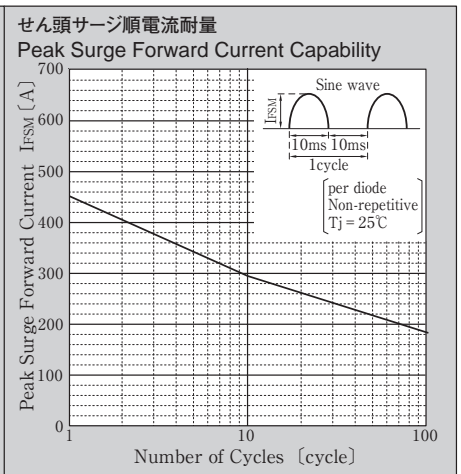
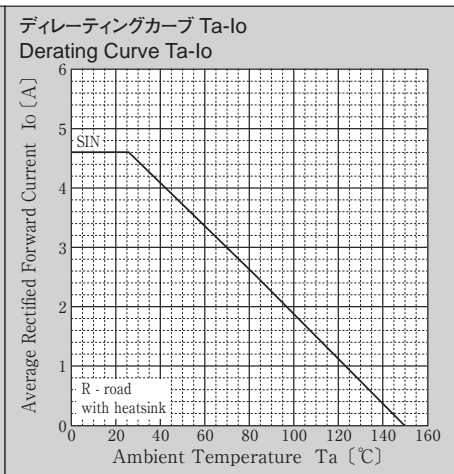
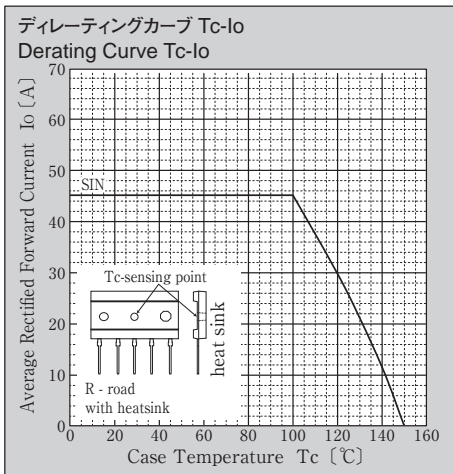
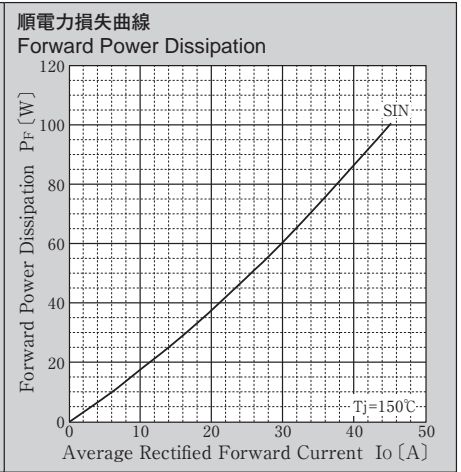
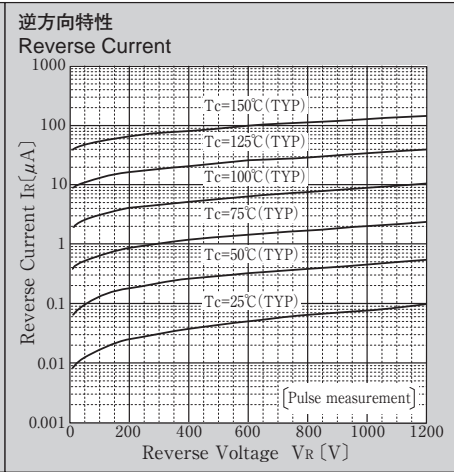
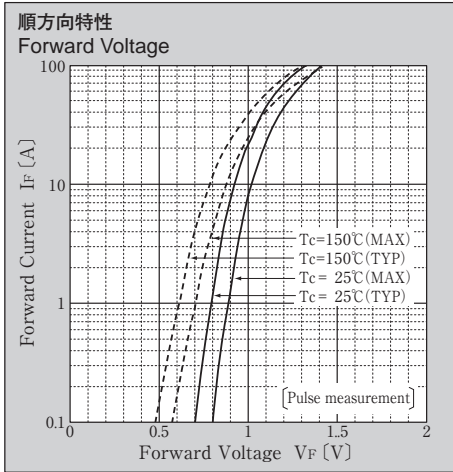
● 絶対最大定格 Absolute Maximum Ratings (指定のない場合は $T_c = 25^\circ\text{C}$ / unless otherwise specified)

項目 Item	記号 Symbol	条件 Conditions		規格値 Ratings	単位 Unit	
保存温度 Storage Temperature	T_{stg}			- 40 ~ 150	$^\circ\text{C}$	
接合部温度 Operating Junction Temperature	T_j			150	$^\circ\text{C}$	
せん頭逆電圧 Maximum Reverse Voltage	V_{RM}			1200	V	
出力電流 Average Rectified Forward Current	I_o	50Hz 正弦波, 抵抗負荷 50Hz sine wave, Resistance load	フィン付き With heatsink	$T_c = 99^\circ\text{C}$	45	A
			フィン無し Without heatsink	$T_a = 25^\circ\text{C}$	4.6	A
せん頭サージ順電流 Peak Surge Forward Current	I_{FSM}	50Hz 正弦波, 非繰り返し 1 サイクルせん頭値, 一素子当たりの規格値, $T_j = 25^\circ\text{C}$ 50Hz sine wave, Non-repetitive 1 cycle peak value, Rating of per diode, $T_j = 25^\circ\text{C}$		450	A	
	I_{FSM1}	$t_p = 1\text{ms}$, 一素子当たりの規格値, $T_j = 25^\circ\text{C}$, 非繰り返し $t_p = 1\text{ms}$, Rating of per diode, $T_j = 25^\circ\text{C}$, Non-repetitive		1423		
電流二乗時間積 Current Squared Time	I^2t	$1\text{ms} \leq t < 10\text{ms}$, 一素子当たりの規格値 $1\text{ms} \leq t < 10\text{ms}$, Rating of per diode		1013	A^2s	
絶縁耐圧 Dielectric Strength	V_{dis}	一括端子・ケース間, AC 1 分間印加 モールド部上面 (端子と平行面) は除く Terminals to case, AC 1 minute Except top (opposite side of the terminal side) of the mold case.		2.5	kV	
締め付けトルク Mounting Torque	TOR	(推奨値: $1.2\text{N}\cdot\text{m}$) (Recommended torque: $1.2\text{N}\cdot\text{m}$)		1.5	$\text{N}\cdot\text{m}$	

● 電氣的・熱的特性 Electrical Characteristics (指定のない場合は $T_c = 25^\circ\text{C}$ / unless otherwise specified)

順電圧 Forward Voltage	V_F	$I_F = 15\text{A}$, パルス測定, 一素子当たりの規格値 Pulse measurement, Rating of Per diode	MAX 1.05	V
逆電流 Reverse Current	I_R	$V_R = 1200\text{V}$, パルス測定, 一素子当たりの規格値 Pulse measurement, Rating of Per diode	MAX 10	μA
熱抵抗 Thermal Resistance	θ_{jc}	接合部・ケース間, フィン付き Junction to case, with heatsink	MAX 0.5	$^\circ\text{C}/\text{W}$
	θ_{ja}	接合部・周囲間, フィン無し Junction to ambient, Without heatsink	MAX 16	$^\circ\text{C}/\text{W}$

■特性図 CHARACTERISTIC DIAGRAMS



* Sine wave は 50Hz で測定しています。
 * 50Hz sine wave is used for measurements.